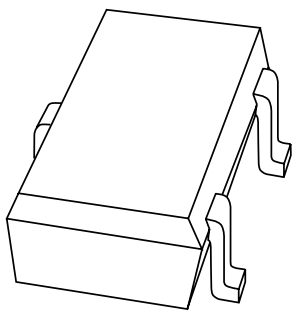


DATA SHEET



BC859W; BC860W PNP general purpose transistors

Product specification
Supersedes data of 1997 Jul 01
File under Discrete Semiconductors, SC04

1997 Sep 03

PNP general purpose transistors

BC859W; BC860W

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- Low noise stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

DESCRIPTION

PNP transistor in a SOT323 plastic package.
NPN complements: BC849W and BC850W.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BC859W	4Dt	BC860W	4Ht
BC859AW	4At	BC860AW	4Et
BC859BW	4Bt	BC860BW	4Ft
BC859CW	4Ct	BC860CW	4Gt

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

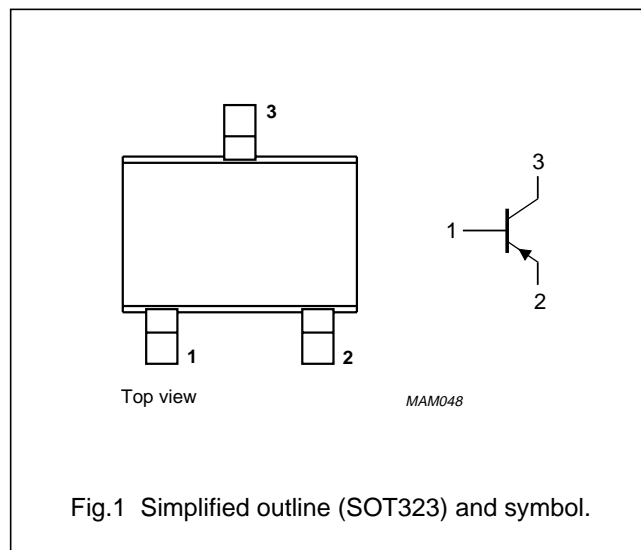


Fig.1 Simplified outline (SOT323) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC859W		–	–30	V
	BC860W		–	–50	V
V_{CEO}	collector-emitter voltage	open base			
	BC859W		–	–30	V
	BC860W		–	–45	V
I_{CM}	peak collector current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	200	mW
h_{FE}	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	125	800	
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	MHz

PNP general purpose transistors

BC859W; BC860W

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859W		–	–30	V
	BC860W		–	–50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859W		–	–30	V
	BC860W		–	–45	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–200	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC859W; BC860W

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

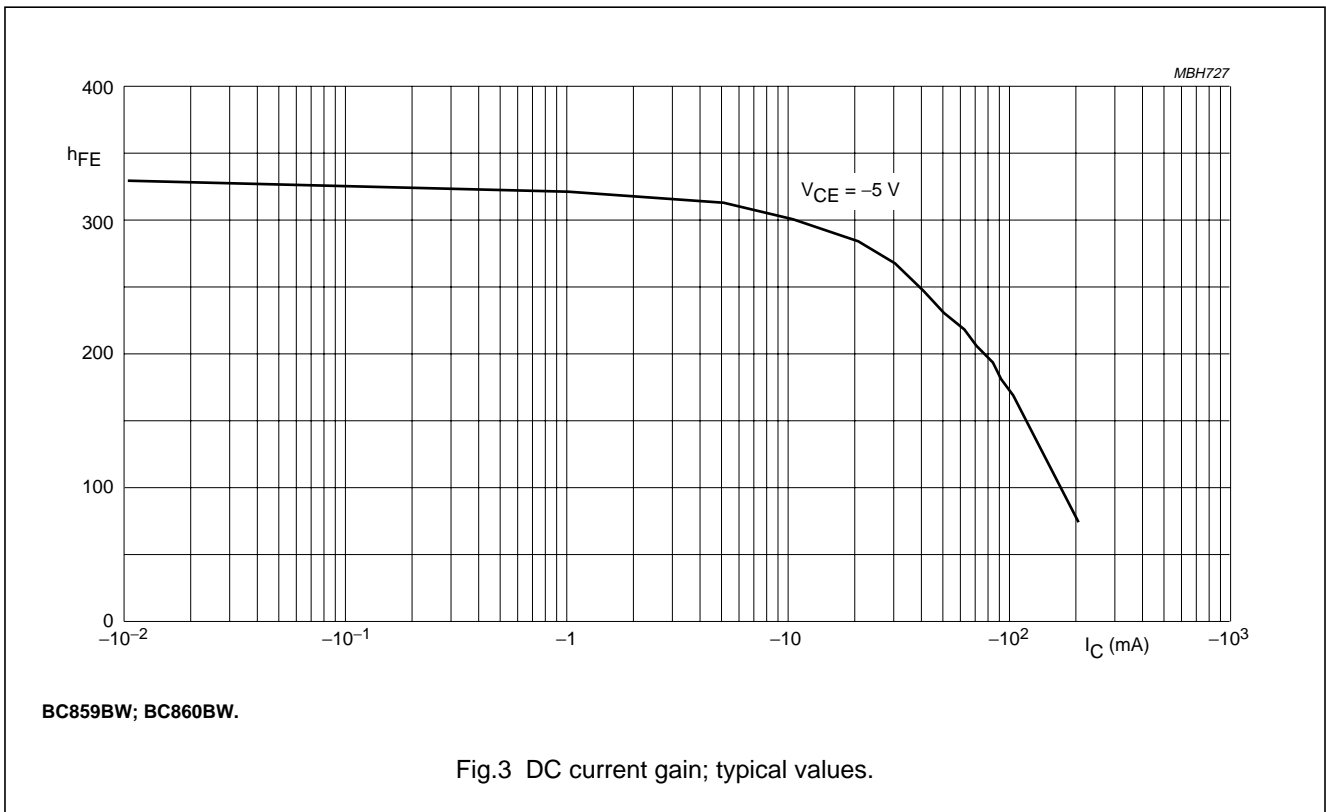
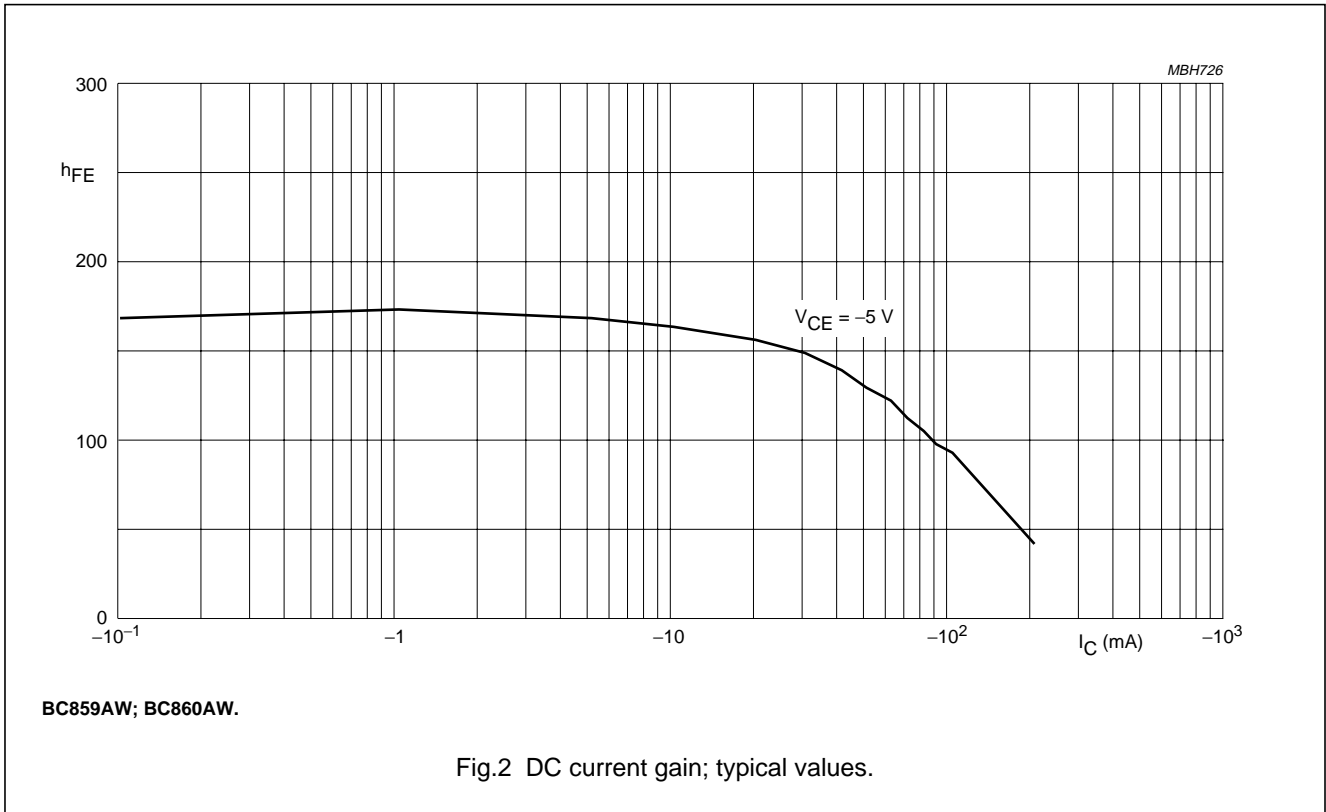
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–	–4	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain BC859W; BC860W BC859AW; BC860AW BC859BW; BC860BW BC859CW; BC860CW	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	800	
			125	–	250	
			220	–	475	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–	–650	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	600	–	750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$	–	–	820	mV
C_C	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	–	5	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure BC859W; BC860W BC859AW; BC860AW	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	10	dB
		$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB
F	noise figure BC859BW; BC860BW BC859CW; BC860CW	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
		$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

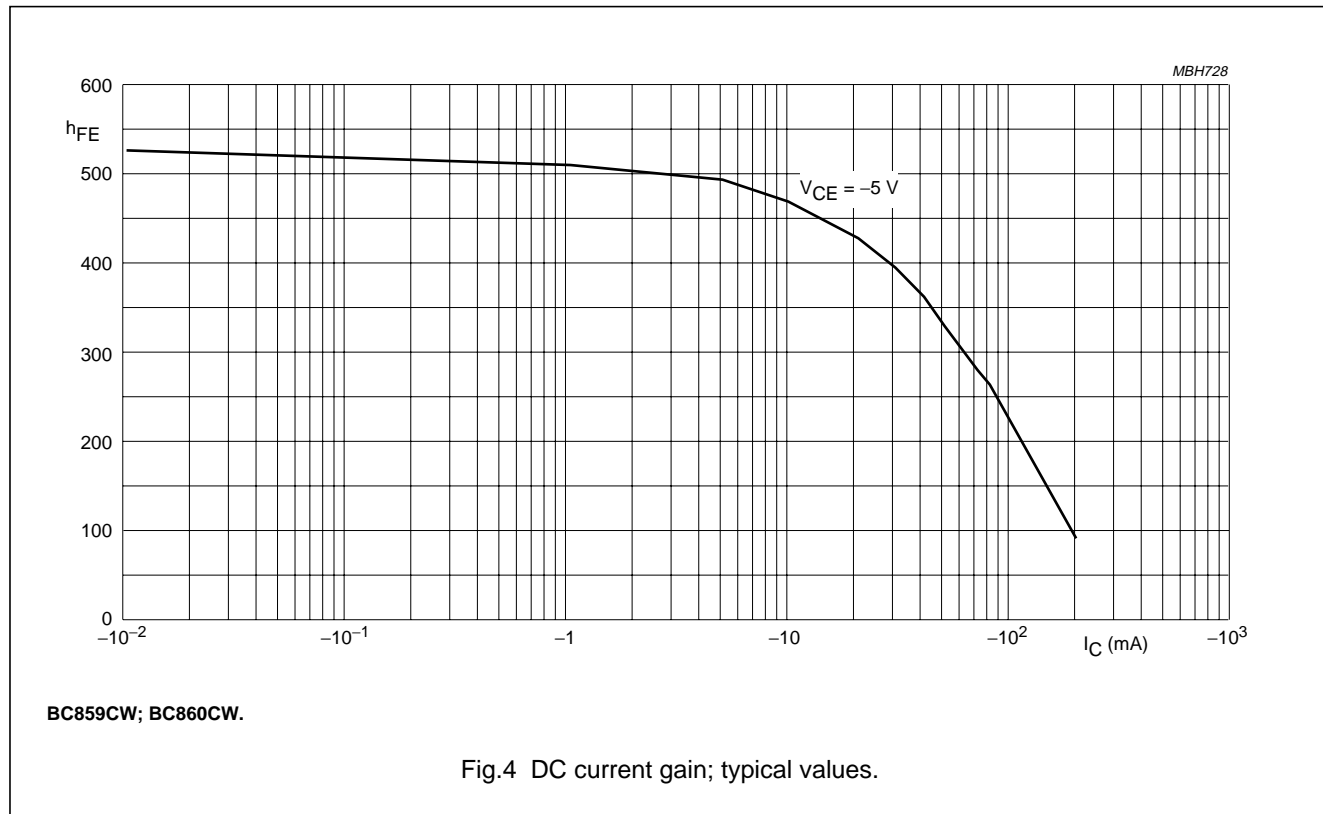
PNP general purpose transistors

BC859W; BC860W



PNP general purpose transistors

BC859W; BC860W



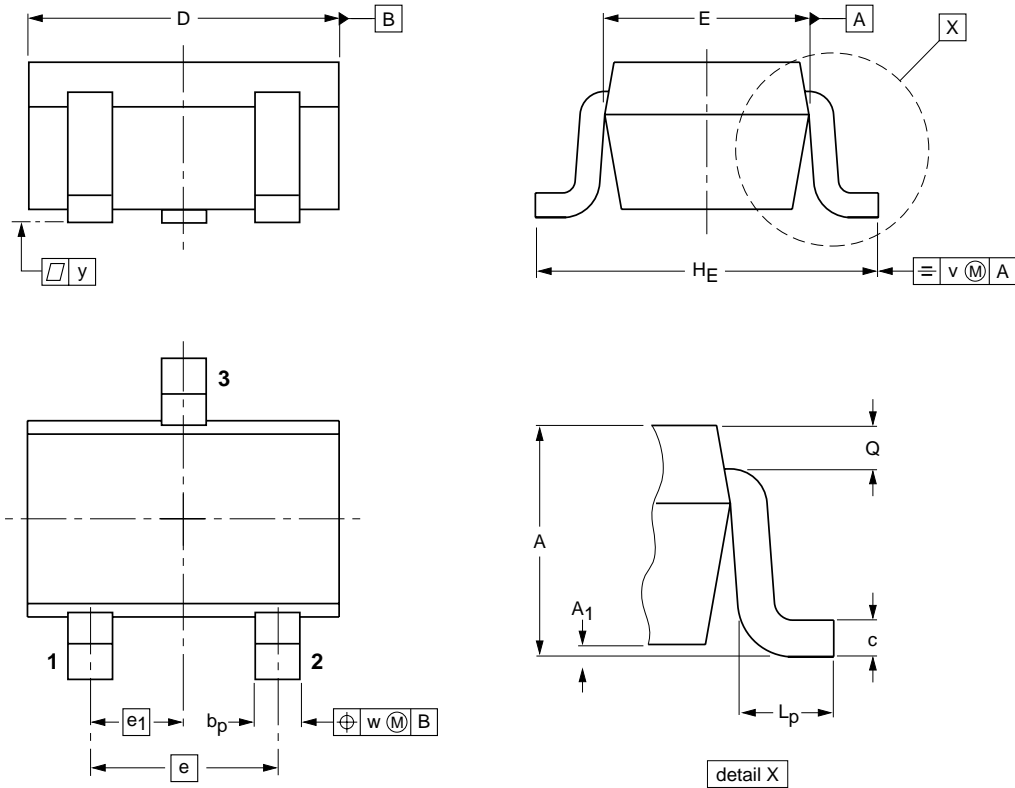
PNP general purpose transistors

BC859W; BC860W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP general purpose transistors

BC859W; BC860W

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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PNP general purpose transistors

BC859W; BC860W

NOTES

PNP general purpose transistors

BC859W; BC860W

NOTES

PNP general purpose transistors

BC859W; BC860W

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